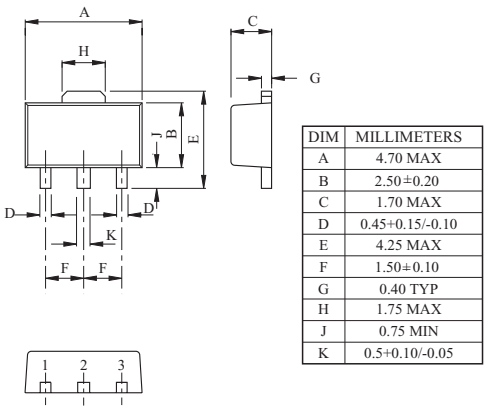
KTA1759

EPITAXIAL PLANAR PNP TRANSISTOR

HIGH VOLTAGE APPLICATION.

FEATURES

· High Breakdown Voltage.



DIM	MILLIMETERS
A	4.70 MAX
B	2.50±0.20
C	1.70 MAX
D	0.45+0.15/-0.10
E	4.25 MAX
F	1.50±0.10
G	0.40 TYP
H	1.75 MAX
J	0.75 MIN
K	0.5+0.10/-0.05

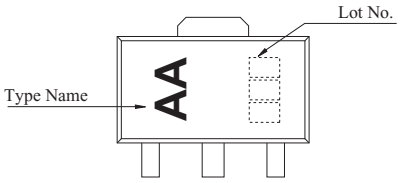
SOT-89

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-400	V
Collector-Emitter Voltage	V_{CEO}	-400	V
Emitter-Base Voltage	V_{EBO}	-7	V
Collector Current	I_C	-100	mA
Collector Power Dissipation	P_C	500	mW
	P_C*	1	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 150	℃

P_C* : Mounted on Ceramic Substrate (250㎟×0.85)

Marking

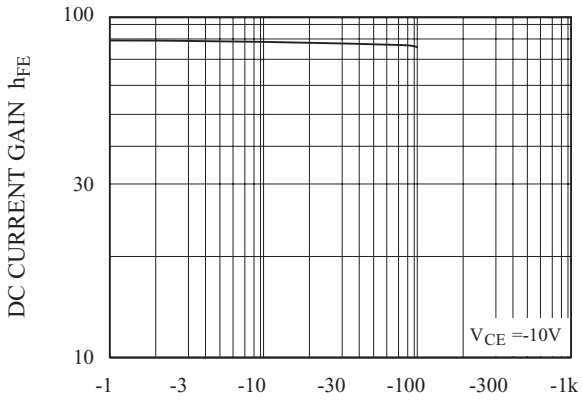


ELECTRICAL CHARACTERISTICS (Ta=25℃)

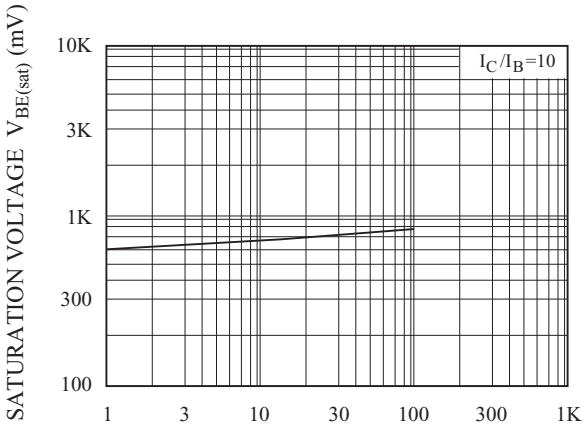
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-50 μA, I_E=0	-400	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-1mA, I_B=0	-400	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-50 μA, I_C=0	-7.0	-	-	V
Collector Cut off Current	I_{CBO}	V_{CB}=-400V, I_E=0	-	-	-10	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=-6V, I_C=0	-	-	-10	μA
DC Current Gain *	h_{FE}	V_{CE}=-10V, I_C=-10mA	50	-	300	
Collector-Emitter Saturation Voltage *	$V_{CE(sat)}$2	I_C=-20mA, I_B=-2mA	-	-	-0.5	V
Base-Emitter Saturation Voltage *	$V_{BE(sat)}$	I_C=-20mA, I_B=-2mA	-	-	-1.5	V

*Pulse Test : Pulse Width≦300 μS, Duty Cycle≦2%

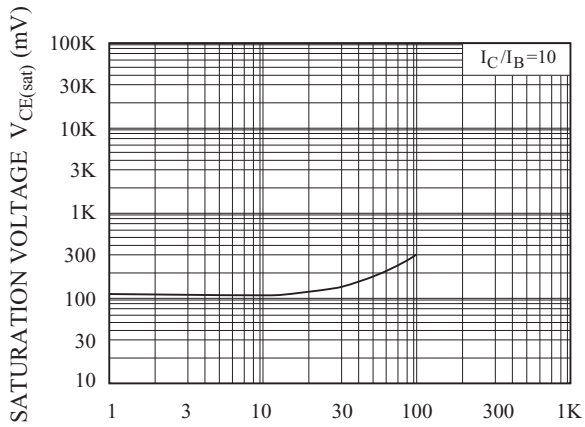
h_{FE} - I_C



$V_{BE(sat)}$ - I_C



$V_{CE(sat)}$ - I_C



C_{ob} - V_{CB}